

Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

5 **Listing of Claims:**

1. (Original): A method for performing read phase auto-calibration of a storage device,
the method comprising:
writing data with at least one predetermined pattern into the storage device;
10 reading the data stored in the storage device by using at least one read phase of a
plurality of read phases;
comparing the read data with the predetermined pattern; and
selecting a read phase from the plurality of read phases according to the comparing
result.
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2. (Original): The method of claim 1, wherein the plurality of read phases are relative to
a reference signal.
3. (Original): The method of claim 2, wherein the reference signal is a strobe signal or a
20 clock signal.
4. (Original): The method of claim 1, wherein the storage device is a dynamic random
access memory (DRAM).
- 25 5. (Original): The method of claim 1, wherein the storage device is a double-data-rate
(DDR) memory.

6. (Original): The method of claim 1, wherein the predetermined pattern is a hexadecimal number which can be equally transformed into to a binary number.
7. (Original): The method of claim 1, wherein the step of reading the data is to read the
5 predetermined pattern stored in the storage device.
8. (Original): The method of claim 1, wherein the step of comparing is to check whether the data read from the storage device match the predetermined pattern.
- 10 9. (Original): The method of claim 1, wherein the read phase selected in the selecting step is determined from the phases without read error among the plurality of read phases.
10. (Original): The method of claim 1, wherein the step of selecting the read phase is to
15 select a middle phase from consecutive phases without read error among the plurality of read phases.
11. (Original): The method of claim 10, wherein the position of the middle phase is at a center position or an approximately center position of the consecutive phases
20 without read error.
12. (Currently Amended): A circuit for performing read phase auto-calibration of a storage device, the circuit comprising:
a control unit coupled to the storage device for determining a ~~[[read]]~~target phase
25 among a plurality of read phases and outputting a multiplexing signal according to the ~~determined read~~target phase;
a delay chain for generating a plurality of delay signals; and

a multiplexer coupled to the control unit and the delay chain for selecting a delay
signal among the delay signals according to the multiplexing signal[.];
wherein the control unit reads data stored in the storage device for at least two times
according to at least two of the read phases and compares the read data with a
predetermined pattern to determine the target phase.

13. (Original): The circuit of claim 12, wherein the control unit is a digital signal
processor.

14. (Original): The circuit of claim 12, wherein the control unit is a firmware.

15. (Cancelled)

16. (New): A circuit for performing read phase auto-calibration of a storage device,
the circuit comprising:
a control circuit coupled to the storage device for reading given data stored in the
storage device according to different read phases, determining a plurality of
consecutive phases among the read phases appropriate for correctly reading the
given data, and determining a target phase among the consecutive phases and
outputting a multiplexing signal according to the target phase;
a delay circuit for generating a plurality of delay signals; and
a multiplexer coupled to the control circuit and the delay circuit for selecting a
delay signal among the delay signals according to the multiplexing signal.

17. (New): The circuit of claim 16, wherein the control circuit is a digital signal
processor.

18. (New): The circuit of claim 16, wherein the control circuit is a firmware.

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19. (New): The circuit of claim 16, wherein the control circuit reads the given data stored in the storage device by using at least two of the read phases and compares the read given data with a predetermined pattern to determine the target phase.

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20. (New): The circuit of claim 16, wherein the target phase is at a center position or an approximately center position of the consecutive phases.

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